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Filling high aspect-ratio nano-structures by atomic layer deposition and its applications in nano-optic devices and integrations
Fabrication of high aspect ratio TiO$_2$ and Al$_2$O$_3$ nanogratings by atomic layer deposition

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The authors report on the fabrication of TiO$_2$ and Al$_2$O$_3$ nanostructured gratings with an aspect ratio of up to 50. The gratings were made by a combination of atomic layer deposition (ALD) and dry etch techniques. The workflow included fabrication of a Si template using deep reactive ion etching followed by ALD of TiO$_2$ or Al$_2$O$_3$. Then, the template was etched away using SF$_6$ in an inductively coupled plasma tool, which resulted in the formation of isolated ALD coatings, thereby achieving high aspect ratio grating structures. SF$_6$ plasma removes silicon selectively without any observable influence on TiO$_2$ or Al$_2$O$_3$, thus revealing high selectivity throughout the fabrication. Scanning electron microscopy was used to analyze every fabrication step. Due to nonreleased stress in the ALD coatings, the top parts of the gratings were observed to bend inward as the Si template was removed, thus resulting in a gradual change in the pitch value of the structures. The pitch on top of the gratings is 400 nm, and it gradually reduces to 200 nm at the bottom. The form of the bending can be reshaped by Ar$^+$ ion beam etching. The chemical purity of the ALD grown materials was analyzed by x-ray photoelectron spectroscopy. The approach presented opens the possibility to fabricate high quality optical metamaterials and functional nanostructures. © 2016 American Vacuum Society. [http://dx.doi.org/10.1116/1.4947586]

I. INTRODUCTION

This work presents the fabrication of periodic nanostructured gratings of TiO$_2$ and Al$_2$O$_3$ with an aspect ratio up to 50 and demonstrates controllable highly selective etching of Si during the TiO$_2$ and Al$_2$O$_3$ grating formation. The procedure combines dry etch and atomic layer deposition (ALD) techniques. ALD is a self-limiting surface reaction method based on sequential and separate introduction of two precursors. Through a repeated cyclic exposure, a thin film is slowly deposited. This is the only technique that allows the deposition of extremely conformal coatings on complex three-dimensional nanostructures. ALD of TiO$_2$ and Al$_2$O$_3$ has been intensively studied and heavily implemented in a variety of applications in physics.

In recent years, the theoretical advances in nanophotonics impose a great demand on developing fabrication techniques that allow patterning of high quality optical materials on nanoscale. High aspect ratio trench structures can serve as one-dimensional photonic crystals (1D PhCs) as an alternative to conventional thin-film multilayers in a vertical strata arrangement. A photonic crystal consisting of a periodic arrangement of high and low refractive index media possesses a photonic bandgap, where light within a certain wavelength range is prohibited to propagate. 1D PhCs by definition have no complete bandgaps opened in all directions inside the structure. Nevertheless, in the reduced space of the wavevectors inside the structure, a PhC may exhibit a unique property of the omnidirectional reflection of external radiation. Such a structure serves, for example, as a bandpass filter. Previously, high aspect ratio vertical 1D PhCs have been realized as Si trench structures and studied for telecommunication wavelengths of around 1.5 μm where Si is transparent. However, Si is not transparent in the visible wavelength region. Therefore, 1D PhCs made of TiO$_2$ and Al$_2$O$_3$ are desirable candidates for applications in the visible and near-infrared regimes. Moreover, the capability to deposit thin films in a conformal way on trench structures can effectively tune a stopband. Such tuning of a photonic bandgap by a third layer (SiO$_2$) has been performed by oxidizing the surface of Si. Fabrication of photonic crystals by ALD can also be applied toward realization of two dimensional PhCs (Ref. 18) as well as other kinds of structured functional materials such as epsilon-near-zero metamaterials. In addition to the advanced deposition of dielectric layers, the deposition capability of metals [e.g., Cu (Ref. 20)] and conductive oxides, [e.g., aluminum-doped...
ZnO (Ref. 21) also provides fabrication flexibility for demands of metamaterials with metal or metallic-like components. Apart from the telecommunication applications, high aspect-ratio vertical 1D PhCs can find various applications ranging from color filters22 to optofluidic sensors for biosensing. In the latter case, liquid flows through trenches, and the refractive index of the liquid is analyzed by a shift of a photonic bandgap.23

In contrast to vertical silicon trenches, the high aspect ratio structures in oxides such as TiO2 and Al2O3 cannot be patterned in the same way by conventional methods such as reactive ion etching (RIE). A recent paper by Huang et al.18 proposed a new method to pattern TiO2. In this approach, ALD has a key role, since patterning formation is based on deposition rather than etching the desired material. The main idea in this method is based on three steps: (1) fabrication of a Si template which is coated by an ALD-deposited film, (2) the ALD film is partially removed by plasma etching techniques, which provides an open access to the original Si template core, and (3) the template is etched away leaving the ALD coated structure with an advance topology. Such a procedure requires high selectivity during the back etching of the template.

II. EXPERIMENT

All the samples were prepared and characterized in a class 100 cleanroom. Si (100) wafers of 150 mm were used as a substrate. The main steps in the gratings manufacturing are shown in Fig. 1. First, the silicon trenches were realized by deep reactive ion etching (DRIE) [Fig. 1(a)]. Then, the trenches were ALD coated [Fig. 1(b)]. After the selective removal of the top parts [Fig. 1(c)], the silicon core between ALD coatings was etched away during the last step. Figure 1(d) represents the final structure, which is the highly anisotropic vertical grating. Each fabrication step was carefully evaluated using cross-sectional scanning electron microscopy (SEM) imaging.

A. Template fabrication

Conventional deep-UV lithography was implemented for defining the grating pattern. The normal procedure includes bottom antireflective coating (BARC) and photoresist coating followed by spray development. To promote adhesion and minimize interference effects, the substrate surface was coated with a 65 nm thick BARC coating (DUV42S-6, Brewer Science, USA) followed by a bake-out at 175 °C for 60 s. The positive photoresist (KRF M230Y, JSR Micro, NV) was spin-coated to a thickness of 360 nm and baked at 130 °C for 90 s. A pitch of 400 nm was chosen for the gratings. The resist was exposed in a Canon FPA-3000 EX4 DUV stepper on field sizes of 2 × 2 cm². In the next step, the silicon trenches were prepared using an advanced DRIE technique.23 Three main steps were used in the Si trench fabrication: etching of the BARC layer, selective silicon etching, and resist removal. The BARC etching step proceeded for 1 min using 40 sccm of oxygen plasma with coil and platen powers of 400 and 20 W, respectively. In the DRIE silicon etch, a Bosch process24 was implemented, where the etching was done by repetitive steps of surface passivation and etching for 2.5 and 5 s, respectively, with a process...
The depth of the trenches was controlled by adjusting the number of cycles. In this work, this depth was kept at 4.5 μm, which with the present etching conditions corresponded to 70 cycles.

The last step in the Si trench fabrication was the removal of the mask photoresist using oxygen plasma for 2 min with a flow of 100 sccm and coil and platen powers of 800 and 20 W, respectively. The depth, pitch, and general shape of the silicon trenches were confirmed by cross-section SEM investigation [Fig. 2(a)].

### B. Atomic layer deposition

The TiO₂ and Al₂O₃ coatings were made in a hot-wall ALD system (Picosun R200). The precursors used for TiO₂ and Al₂O₃ deposition were titanium tetrachloride (TiCl₄) and trimethylaluminum Al(CH₃)₃, respectively (supplied by Sigma Aldrich). Deionized water was used as oxidant source in both processes. In the case of TiO₂ deposition, the temperature of 150 ºC was chosen in order to minimize the TiO₂ surface roughness caused by crystalline anatase transition known to occur at high temperatures.²⁵ The growth rates of TiO₂ and Al₂O₃ coatings were found to be 0.045 and 0.089 nm/cycle, respectively, (in agreement with the previously reported data)²⁶ using varying-cycles deposition with ellipsometric characterization of the film thicknesses and refractive indices (VASE, J.A. Woollam Co.). No significant variations of deposition rates were observed. ALD recipes for TiO₂ and Al₂O₃ are represented in Tables II and III. The same precursor was introduced twice into the chamber in order to ensure successful diffusion to the bottom of the trenches. In order to grow 90 nm coatings, 2000 and 1000 cycles were used for TiO₂ and Al₂O₃, respectively. Figure 2(b) shows a cross-section SEM micrograph, which reveals the high quality conformal coatings.

### C. Removal of the top part and template back etching

The top TiO₂ and Al₂O₃ layers were removed by inductive coupled plasma (ICP). Etching of TiO₂ and Al₂O₃ in ICP systems were previously reported,²⁷,²⁸ especially etch of Al₂O₃ received attention due to its beneficial use as a hard mask and a gate dielectric.²⁸ In the case of TiO₂, a Cl₂ flow was used. The removal of Al₂O₃ involved BCl₃ and Cl₂. First, the removal of TiO₂ and Al₂O₃ was investigated on planar Si substrates. Al₂O₃ of 145 nm and 90 nm of TiO₂ were deposited on silicon and etched using recipes described in Table IV. The remaining thickness of deposited layers was measured using spectroscopic ellipsometry versus process time. The results are summarized in Figs. 3(a) and 3(b). The etch rates of TiO₂ and Al₂O₃ following these recipes are

### Table I. DRIE parameters for Si trench fabrication.

<table>
<thead>
<tr>
<th>Process gas flow (sccm)</th>
<th>Passivation (5 s)</th>
<th>Etching (2.5 s)</th>
</tr>
</thead>
<tbody>
<tr>
<td>C₂F₆</td>
<td>50</td>
<td>20</td>
</tr>
<tr>
<td>SF₆</td>
<td>—</td>
<td>60</td>
</tr>
<tr>
<td>O₂</td>
<td>—</td>
<td>5</td>
</tr>
</tbody>
</table>

---

Fig. 2. (a) Fabricated silicon trenches. (b) ALD coating of TiO₂. (c) Selective opening of the top parts of the gratings. (d) Fabricated TiO₂ and (e) Al₂O₃ gratings.
0.11 and 0.89 nm/s, respectively. It is important to strictly control the etching of the top part of TiO$_2$ and Al$_2$O$_3$ since an overetch can damage the silicon core beneath the ALD coatings and the control of the grating fabrication can be lost, due to the fact that the depth of the Si core will become unknown. The TiO$_2$ grating after removal of the top part but still with the Si template can be seen in Fig. 2(c).

The subsequent selective silicon etching (template removal) proceeded using a continuous isotropic silicon etch in the ICP etch system based on SF$_6$ at a substrate temperature of 20°C. This process exhibits an extreme selectivity with respect to oxides and selectivity of Si to Al$_2$O$_3$ was previously reported to be 66 000:1 in SF$_6$ ICP plasma. Table IV summarizes the process. Figure 3(c) shows the etch depth as a function of time. Controlling the time is essential, since overetching will lead to collapse of the gratings. The coil power can be reduced in order to slow down silicon etching. However, reducing it below 300 W results in nonuniform etching across the sample. Figures 2(d) and 2(e) show SEM cross-sections of the fabricated nanostructured TiO$_2$ and Al$_2$O$_3$ gratings.

### III. RESULTS AND DISCUSSION

The TiO$_2$ and Al$_2$O$_3$ nanostructured gratings were successfully grown and isolated on the Si substrates. The SEM cross-section investigation [Figs. 2(a)–2(e)] reveals high selectivity and precise control in all steps throughout the fabrication. With the thickness of Al$_2$O$_3$/TiO$_2$ coatings of 90 nm and gratings height of 4500 nm, the aspect ratio of the fabricated nanostructures is 1:50.

During DRIE, the substrate suffers from the scallops formed during the first 5–10 etching cycles. These scallops are typical for the Bosh etch process, and cause the undesired roughness of the subsequent ALD coatings. After these first DRIE cycles, the etching proceeds smoothly with only a very small variation of the Si trench width. The thickness of the fabricated Si walls at the bottom is 100 nm, while at the very top 150 nm. The variation of the wall thickness mainly occurs during DRIE of the first micrometer depth.

#### Table II. Recipe for one cycle of TiO$_2$.

<table>
<thead>
<tr>
<th>Precursor</th>
<th>Carrier gas flow (sccm)</th>
<th>Pulse (s)</th>
<th>Purge (s)</th>
</tr>
</thead>
<tbody>
<tr>
<td>TiCl$_4$</td>
<td>150</td>
<td>0.1</td>
<td>0.5</td>
</tr>
<tr>
<td>TiCl$_4$</td>
<td>150</td>
<td>0.1</td>
<td>20</td>
</tr>
<tr>
<td>H$_2$O</td>
<td>200</td>
<td>0.1</td>
<td>0.5</td>
</tr>
<tr>
<td>H$_2$O</td>
<td>200</td>
<td>0.1</td>
<td>20</td>
</tr>
</tbody>
</table>

#### Table III. Recipe for one cycle of Al$_2$O$_3$.

<table>
<thead>
<tr>
<th>Precursor</th>
<th>Carrier gas flow (sccm)</th>
<th>Pulse (s)</th>
<th>Purge (s)</th>
</tr>
</thead>
<tbody>
<tr>
<td>TMA$^a$</td>
<td>150</td>
<td>0.1</td>
<td>0.5</td>
</tr>
<tr>
<td>TMA</td>
<td>150</td>
<td>0.1</td>
<td>20</td>
</tr>
<tr>
<td>H$_2$O</td>
<td>200</td>
<td>0.1</td>
<td>0.5</td>
</tr>
<tr>
<td>H$_2$O</td>
<td>200</td>
<td>0.1</td>
<td>20</td>
</tr>
</tbody>
</table>

$^a$Trimethylaluminum, Al(CH$_3$)$_3$

### Table IV. Recipes for Al$_2$O$_3$, TiO$_2$, and Si in ICP etch system.

<table>
<thead>
<tr>
<th>Process parameters$^a$</th>
<th>TiO$_2$ etch</th>
<th>Al$_2$O$_3$ etch</th>
<th>Si etch</th>
</tr>
</thead>
<tbody>
<tr>
<td>Cl$_2$ (sccm)</td>
<td>30</td>
<td>1.2</td>
<td>—</td>
</tr>
<tr>
<td>BCl$_3$ (sccm)</td>
<td>—</td>
<td>6.8</td>
<td>—</td>
</tr>
<tr>
<td>SF$_6$ (sccm)</td>
<td>—</td>
<td>—</td>
<td>90</td>
</tr>
<tr>
<td>Pressure (mTorr)</td>
<td>3</td>
<td>4</td>
<td>10</td>
</tr>
<tr>
<td>Coil power (W)</td>
<td>900</td>
<td>1200</td>
<td>400</td>
</tr>
<tr>
<td>Platen power (W)</td>
<td>50</td>
<td>200</td>
<td>3</td>
</tr>
</tbody>
</table>

$^a$Process temperature is 20°C for all processes.

ALD of 90 nm Al$_2$O$_3$ and TiO$_2$ revealed very high quality layers with no noticeable variation in thickness, despite the very high aspect ratio of DRIE etched Si trenches.

![Fig. 3. (Color online) Etch rate measurements of ALD layers on planar Si substrates for (a) TiO$_2$ using Cl$_2$ based etching and (b) Al$_2$O$_3$ using Cl$_2$/BCl$_3$ based etching, respectively. (c) Depth of silicon vs time during Si template removal in ICP using SF$_6$.](image-url)
tions [Fig. 4(a)], whereas the TiO2 film contained around chemically high quality films with no observable contamination.

The back etch of the original silicon template using the alternative for ALD of TiO2 at 150°C must be considered as unreacted TiCl4 precursor [Fig. 4(b)]. The presence of chlorine residuals, which originate from the unreacted TiCl4 precursor [Fig. 4(b)], is revealed. Case (b) shows a small (1–3 at. %) amount of Cl2 incorporated into TiO2 sample.

For evaluating the chemical composition, ALD of TiO2 and Al2O3 was made on planar Si substrates. The planar structures were analyzed by x-ray photoelectron spectroscopy (XPS) in order to detect possible impurities in the chemical composition (Fig. 4). Al2O3 samples revealed chemically high quality films with no observable contamination [Fig. 4(a)], whereas the TiO2 film contained around 2–3 at. % of chlorine residuals, which originate from the unreacted TiCl4 precursor [Fig. 4(b)]. The presence of chlorine can be reduced to below the detection level of the XPS measurement at ALD growth temperatures around 300°C. However, such high growth temperatures lead to the crystalline anatase phase transition, which will heavily increase coating roughness. Chlorine free precursors such as Titaniumtetraisopropoxide (TTIP) must be considered as an alternative for ALD of TiO2 at 150°C and below.

The removal of the top part has to be done with care since the silicon beneath the TiO2 and Al2O3 coatings immediately will start to be etched by the Cl2 or Cl2/BCl3 based plasma. The back etch of the original silicon template using the isotropic dry etching recipe based on continuous SF6 process shows no significant height differences of the fabricated gratings across the sample. This process, however, is nonlinear and very sensitive to the coil power of the ICP tool [Fig. 3(c)]. A coil power of 400 W was the most optimum, since decreasing below 300 W leads to larger deviations of the height of the remaining Si core and increasing above 400 W results in a higher etching speed and less control of the etching conditions. The nonlinearity during Si core removal represented in Fig. 3(c) puts a demand on controlling the condition during the previous TiO2/Al2O3 top opening step. During silicon etching between the ALD coating steps, no influence on the TiO2/Al2O3 thin film morphology has been observed as a result of the very selective Si etch. This is a rather significant result since it opens the opportunity to fabricate similar structures using other materials by using the right chemical selectivity and the possibility of ALD growth. The fabricated Al2O3 and TiO2 gratings have a shape similar to the surface of the original Si template. Due to the highly conformal nature of the ALD growth, the shape of the scallops from the silicon template is transferred to the ALD grown gratings.

IV. SUMMARY AND CONCLUSIONS

To summarize, vertically nanostructured TiO2 and Al2O3 gratings were fabricated. The present work demonstrates the powerful combination of conformal ALD growth of dielectric layers on a high aspect ratio Si template and subsequent highly selective etching of the Si template. Silicon etching is an isotropic process which makes it extremely flexible to the realization of different types of 3D ALD structures such as trenches, pillars, pores, etc. Combining DRIE and ALD, it is possible to create vertical oxides nanogratings with such a high aspect ratio, which is not possible to obtain by any other
technique. Additionally, it is also possible to create high ratio ternary compounds such as Al$_x$Ti$_y$O$_z$, with different constituent concentrations by varying TMA and TiCl$_4$ cycles in the ALD recipes. It will allow the tailoring of the effective TiO$_2$ are good candidates for 1D PhCs in the visible and defined high aspect ratio trench structure made of Al$_2$O$_3$ and their roughness and changing the top shape. The well-which allows tuning the top part of the gratings, minimizing combination with development of new DRIE recipes with separation of the gratings lamina. This should be handled in properties.

As for the outlook, further work is needed on the top sep-

ature related to possible output of grating structures.

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The authors would like to thank process specialists from Danish National Center for Micro- and Nanofabrication (DANCHIP) E. Khomtchenko and M. Keil for all work related to deep UV lithography. The authors acknowledge P. Shi for fruitful discussions and practical recommendations and R. Malureanu, A. Andryieuski, and S. Zhukovsky for the ideas related to possible output of grating structures.

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